		•	•	Exp	ress Mail L	abel No. EL	713 631	849 US	
FØRM PTO-1449				Docket Number (Optional) 81839.0108		Application Number Not Assigned			
INF	ORMATION DISCLOSURI			Applicant	Takehito USHI	KI; Hitoshi TSU	INODA	1.8008	
(Use several sheets if necessary)				Filing Date December 11, 2001		Group Art Unit Not Assigned		101	
		U.S. PATEN	NT D	OCUMENTS	3			<del></del>	
EXAMINER INITIAL	DOCUMENT NUMBER	DATE		NAME CL		SUBCLASS	FILING DATE IF APPROPRIATE		
92	5,447,890	09/1995	Kato	et al.	437	249			
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	F	OREIGN PAT	ENT	DOCUMEN	TS				
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42	EP 0782179	7/02/1997		EPO			X	NO	
İ	₽ EP 0337556	10/18/1989		EPO		-	х		
	•WO 8912318	12/14/1989		PCT			×		
	₄ EP 0764976	03/26/1997		EPO			x		
AL	→ JP06-114664	04/26/1994		JAPAN			Abstract		
	OTHER DOCUME	NTS (Including A	uthor	, Title, Date, Pei	rtinent Pages,	Etc.)			
S.l	Current Status of 200 mm and 300 mm Silicon Wafers; Howard R. Huff et al.,; 1998 Publication Board, Japanese Journal of Applied Physics; vol. 37, part 1, No. 3B March 1998; pp 1210-1216;								
48	Thickness Considerations in Direct Silicon Wafer Bonding; Q.Y. Tong et al., J. Electrochem. Soc., Vol. 142, No. 11; November 1995								

EXAMINER	Id	DATE CONSIDERED	5/14/02
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EXAMINER: Initial if citation considered, whether or not citation is in conformance with MPEP § 609; Draw line through citation if not in conformance and not considered. Include copy of this form with next communication to the applicant.